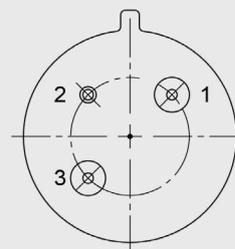
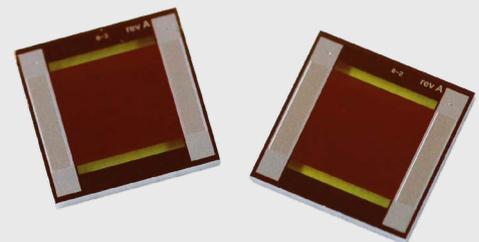
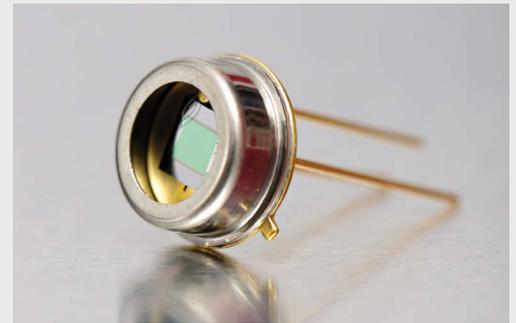


Fast radiation source for use with thermopiles and pyroelectric detectors in NDIR gas analysis and other applications.

MEMS Infrared Radiation Source C-MOSI®-500

| | | |
|--|--|-----------------|
| Active Area | 2.2 x 2.3 | mm ² |
| Hot Resistant | 19 ± 5 | Ω |
| Temperature Coefficient¹ | typ. 1250 | ppm/K |
| Time Constant | typ. 15 | ms |
| Nominal Input Power | 600 | mW |
| Operation Voltage² | typ. 3.4 | V |
| Operation Current² | typ. 175 | mA |
| Active Area Temperature^{3,5} | 650 | °C |
| Spectral Output Range⁶ | 2 - 15 | μm |
| Mass | ~ 1 | g |
| Housing | TO39 (modified) | |
| Expected Lifetime^{4,5} | > 5,000 h at 800 °C > 100,000 h at 650 °C | |



Pin Assignment
(bottom view)

Pin 1 Power
Pin 2 Case
Pin 3 Power

The current data are based on simulations and tests. They are subject to change during the next evaluation steps.

- ¹ 0 °C - 700 °C
- ² at 19 Ω
- ³ at nominal power (0.6 W)
- ⁴ at 10 Hz, 50 % duty cycle, MTTF 63 % (membrane fracture)
- ⁵ at T_{amb} = 25 °C
- ⁶ without window

Absolute Max. Rating

| | | |
|-------------------------|-----|----|
| Input Power | 900 | mW |
| Housing Temperature | 200 | °C |
| Active Area Temperature | 800 | °C |

March 1st 2018 – technology revision 2 – subject to change without notice

